

IN THE TITLE

Please delete the title in its entirety and replace with --METHOD OF FORMING A LOW INDUCTANCE HIGH CAPACITANCE CAPACITOR--.

IN THE SPECIFICATION

On page 1 first line please insert -- This is a Divisional Application of Serial No.: 09/740,781 filed December 19, 2000, ^{now Patent No. 6,631,540} which is a Continuation of Application Serial No.: 09/447,915 filed November 23, 1999, ^{now Patent No. 6,262,877} --

IN THE CLAIMS

Please cancel claims 1-23 without prejudice.

Please add new claims 24-30.

24. (New) A method of forming a capacitor, comprising
attaching a first plurality of terminals to a first surface of a porous Ta block;
masking a portion of each of the first plurality of terminals;
oxidizing the unmasked portions of the Ta block;
forming a second electrode over the oxidized Ta; and
attaching a second plurality of terminals to the second electrode;
wherein the second plurality of terminals are attached to the same side
of the capacitor as the first plurality of terminals.

25. (New) The method of Claim 24, further comprising attaching a third plurality of terminals to the first electrode and a fourth plurality of electrodes to the second electrode.